

Page 9, paragraph beginning at line 27:

As mentioned in the above description of the present invention, a polysilicon film containing Ni having a density in the range of [[ranges]] 2×10^{17} and 5×10^{19} atoms/cm³ consists of needle shaped silicon crystallites, and the whole part of the polysilicon film is crystallized uniformly.

REMARKS

At the outset, the Examiner is thanked for the thorough review and consideration of the subject application. The Final Office Action of January 14, 2002 has been received and contents carefully reviewed.

The Examiner objected to the amendment filed November 20, 2001 under 35 USC § 132 stating that it introduces new matter into the disclosure. The Examiner rejected claims 1, 3, 6, and 9 under 35 USC § 112, first paragraph, as containing subject matter which was not described in the specification. Applicants respectfully traverse the objection and the rejection.

Applicants amended the specification and claims by changing “bar-like” to “needle-shaped” in response to the rejection under 35 USC § 112, second paragraph. The recitation of “needle-shaped silicon crystallites” is supported in the specification at least 9 in Figures 11A-D and 12A-C of this application, and therefore is also supported in the specification. In contrast to the Examiner’s definition, the crystallite, as described in the specification of this application, grows from a nucleus for crystallization in a certain direction by the movement of NiSi₂ in the early stage of crystallization, respectively. This crystallite having a needle shape grows continuously until this crystallite collides with other crystallites grown from